

RJL60S5DPP-E0

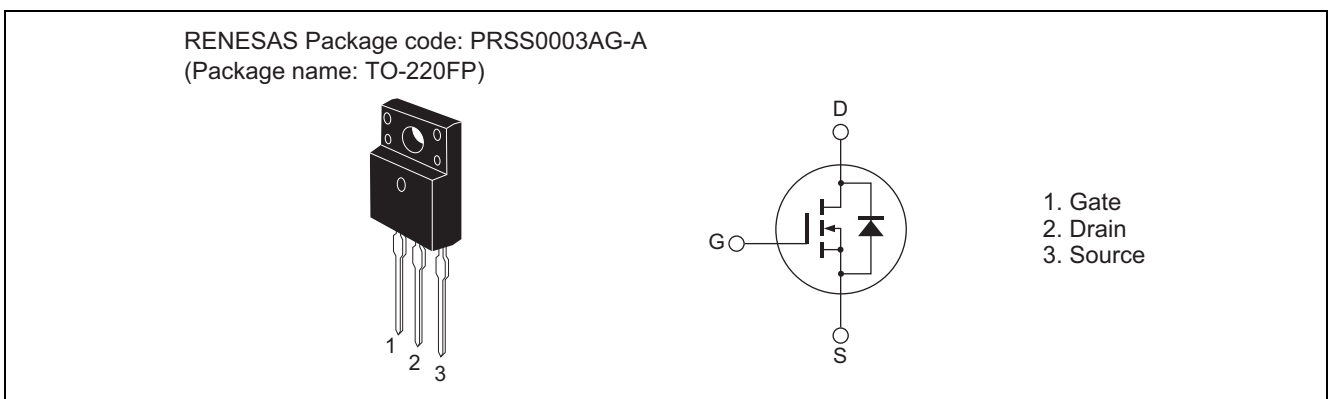
600V - 20A - SJ MOS FET
High Speed Power Switching

R07DS0819EJ0100
Rev.1.00
Feb 04, 2013

Features

- Superjunction MOSFET
- Built-in fast recovery diode
 $t_{rr} = 170 \text{ ns typ. (at } I_F = 20 \text{ A, } V_{GS} = 0, di_F/dt = 100 \text{ A}/\mu\text{s, } T_a = 25^\circ\text{C)}$
- Low on-resistance
 $R_{DS(on)} = 0.15 \Omega \text{ typ. (at } I_D = 10 \text{ A, } V_{GS} = 10 \text{ V, } T_a = 25^\circ\text{C)}$

Outline



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	+30, -20	V
Drain current	$T_C = 25^\circ\text{C}$	I_D^{Note1}	20
	$T_C = 100^\circ\text{C}$	I_D^{Note1}	12.6
Drain peak current	$I_{D(pulse)}^{\text{Note1}}$	40	A
Body-drain diode reverse drain current	I_{DR}^{Note1}	20	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}^{\text{Note1}}$	40	A
Avalanche current	I_{AP}^{Note2}	4	A
Avalanche energy	E_{AR}^{Note2}	0.87	mJ
Channel dissipation	P_{ch}^{Note3}	33.7	W
Channel to case thermal impedance	θ_{ch-c}	3.7	$^\circ\text{C}/\text{W}$
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes: 1. Limited by T_{ch} max.
2. $ST_{ch} = 25^\circ\text{C}$, $T_{ch} \leq 150^\circ\text{C}$
3. Value at $T_c = 25^\circ\text{C}$

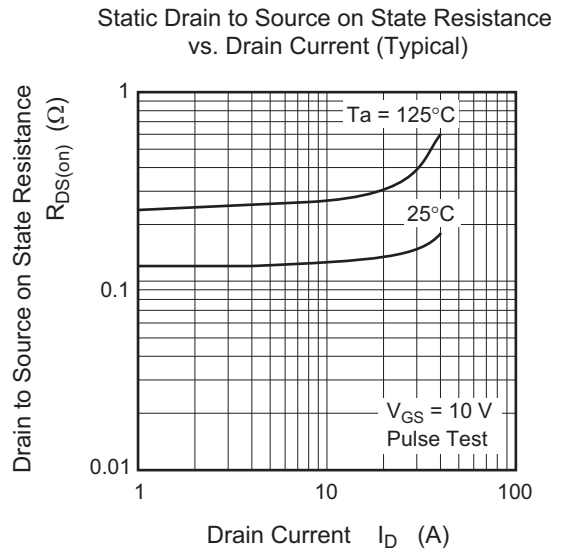
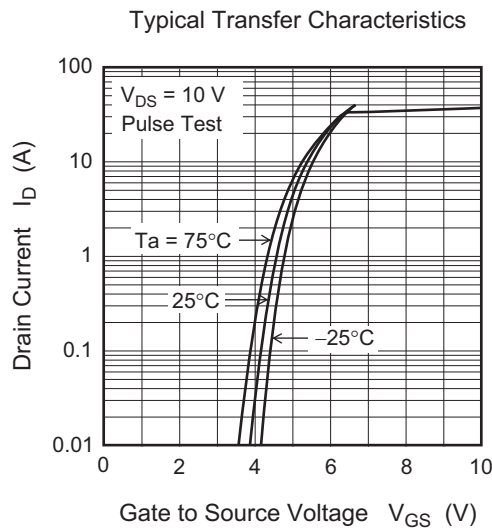
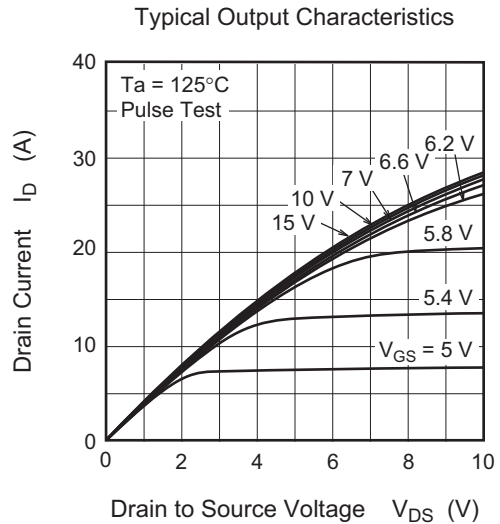
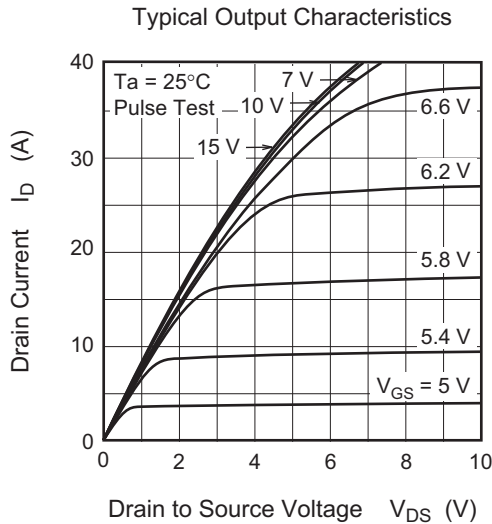
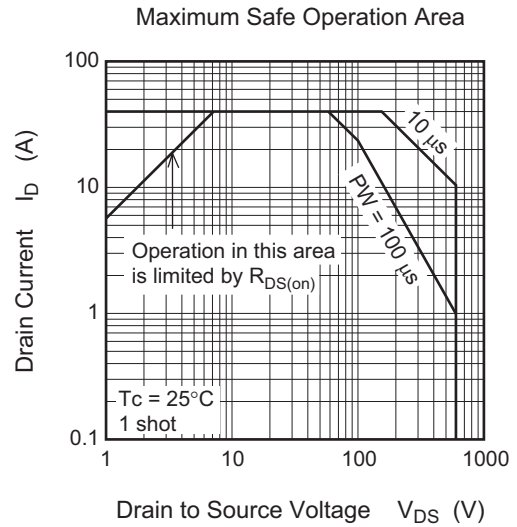
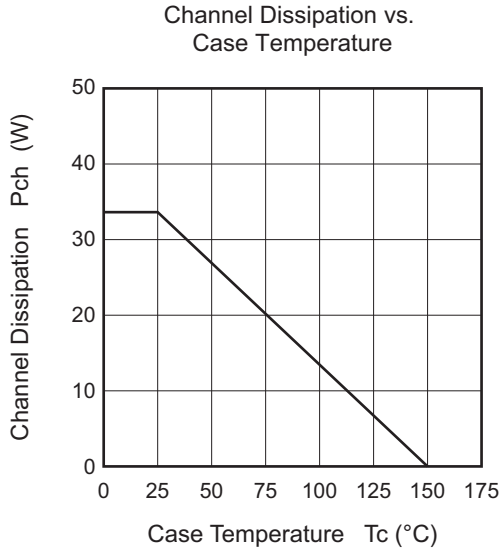
Electrical Characteristics

(Ta = 25°C)

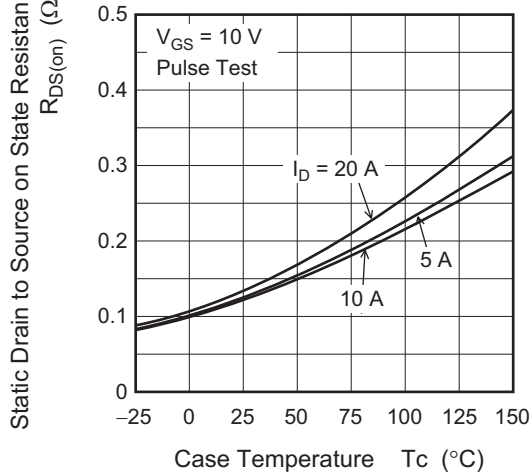
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	mA	$V_{DS} = 600 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = +30\text{V}$, -20 V , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3	—	5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.150	0.178	Ω	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	0.375	—	Ω	Ta = 150°C $I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
Gate resistance	Rg	—	4.5	—	Ω	f = 1 MHz $V_{DS} = 25 \text{ V}$, $V_{GS} = 0$
Input capacitance	Ciss	—	1700	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	Coss	—	2200	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	18	—	pF	f = 100kHz
Turn-on delay time	$t_{d(on)}$	—	22	—	ns	$I_D = 10 \text{ A}$
Rise time	t_r	—	31	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	101	—	ns	$R_L = 30 \Omega$
Fall time	t_f	—	27	—	ns	$R_g = 10 \Omega$ ^{Note4}
Total gate charge	Qg	—	46	—	nC	$V_{DD} = 480 \text{ V}$
Gate to source charge	Qgs	—	11	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Qgd	—	23	—	nC	$I_D = 20 \text{ A}$ ^{Note4}
Body-drain diode forward voltage	V_{DF}	—	1.0	1.6	V	$I_F = 20 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	170	—	ns	$I_F = 20 \text{ A}$
Body-drain diode reverse recovery current	I_{rr}	—	13	—	A	$V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ ^{Note4}
Body-drain diode reverse recovery charge	Q _{rr}	—	1.2	—	μC	

Notes: 4. Pulse test

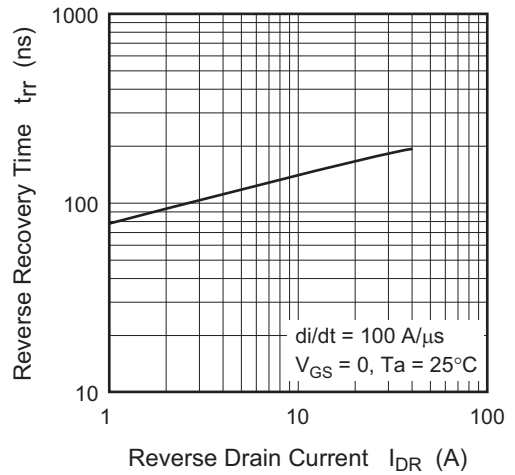
Main Characteristics



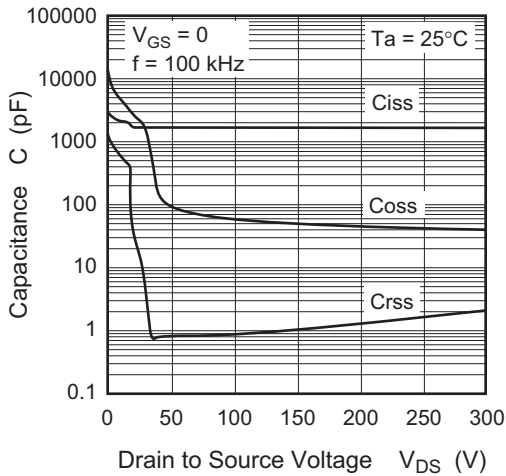
Static Drain to Source on State Resistance vs. Temperature (Typical)



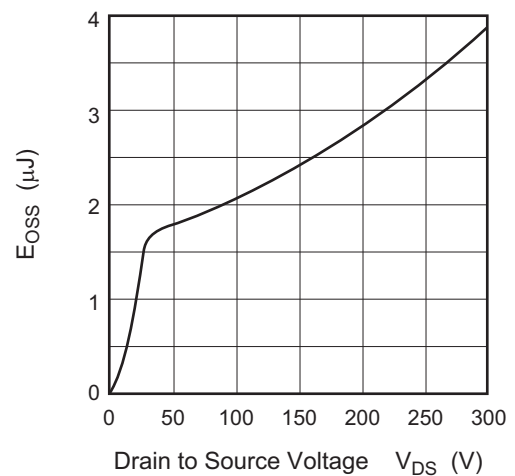
Body-Drain Diode Reverse Recovery Time (Typical)



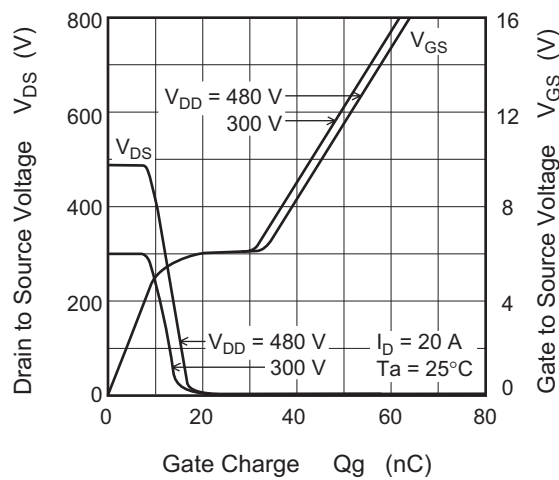
Typical Capacitance vs. Drain to Source Voltage



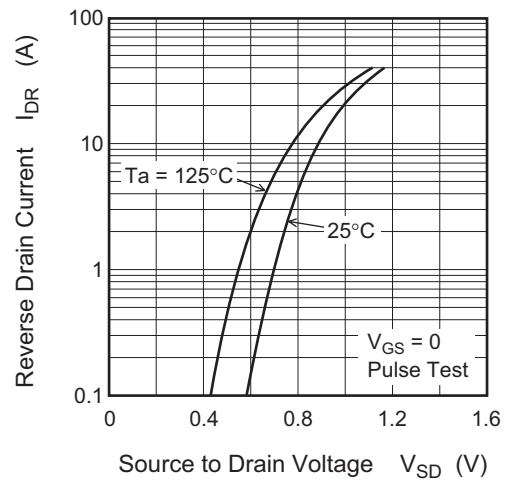
C_OSS Stored Energy (Typical)

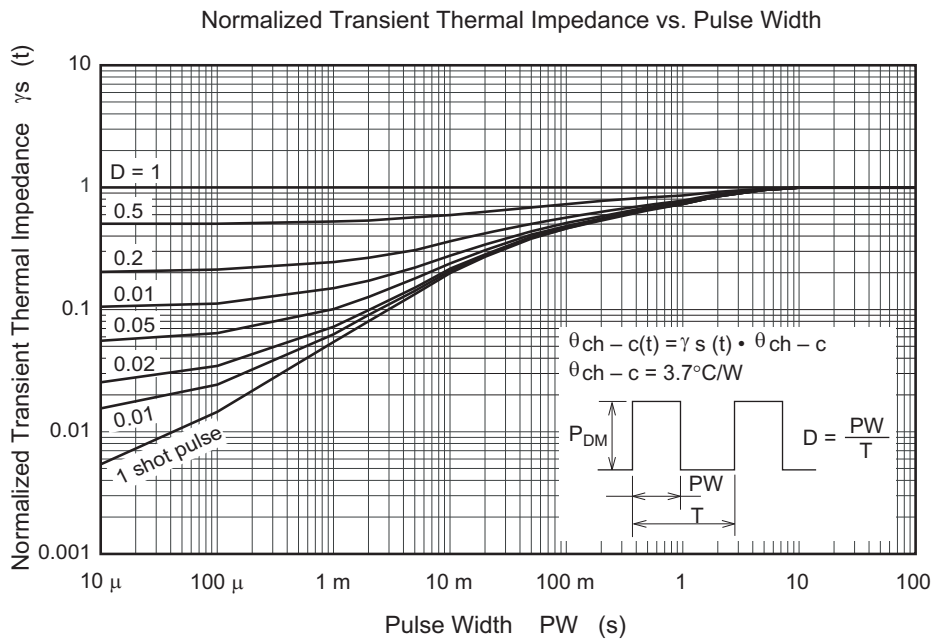
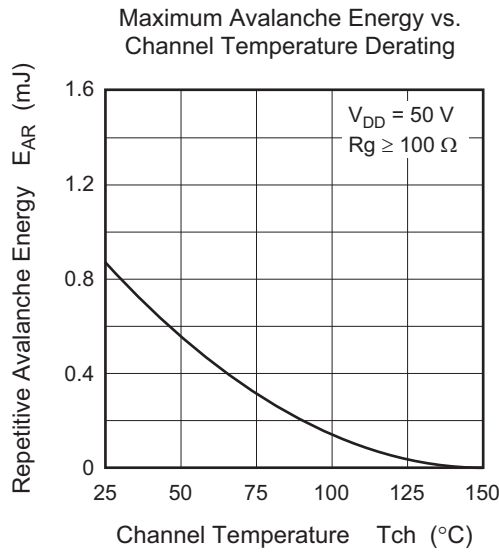
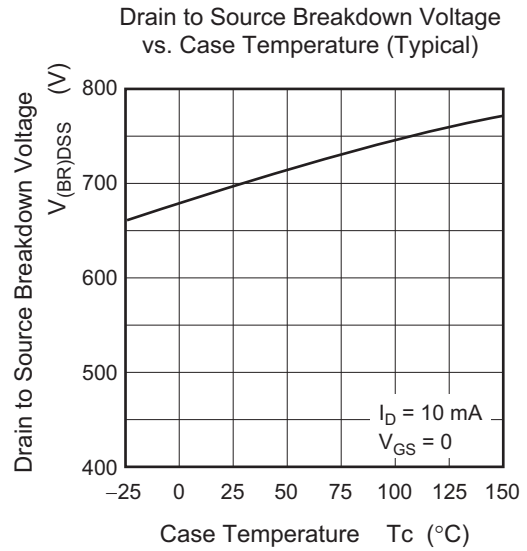
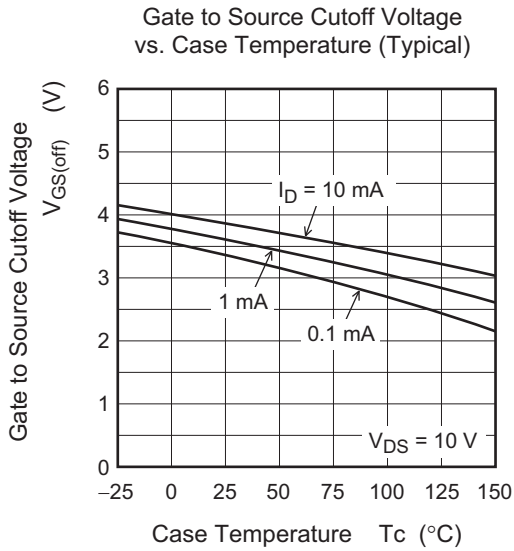


Dynamic Input Characteristics (Typical)

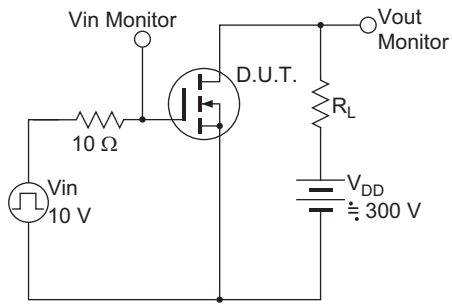


Reverse Drain Current vs. Source to Drain Voltage (Typical)

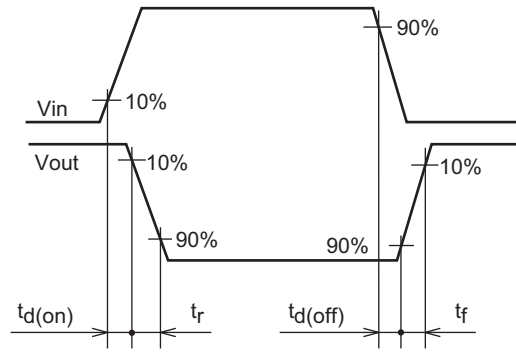




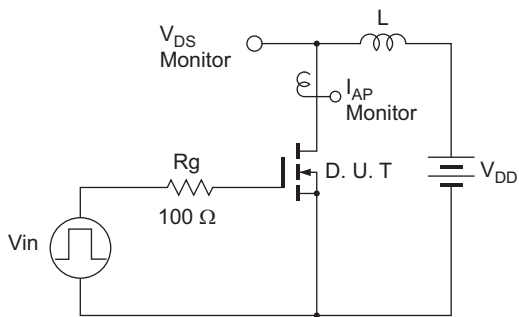
Switching Time Test Circuit



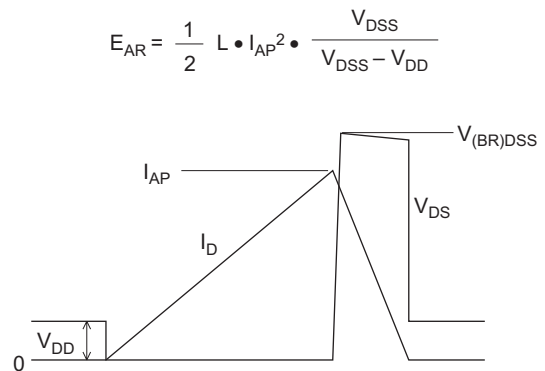
Waveform



Avalanche Test Circuit



Avalanche Waveform



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